MCH6448

Power MOSFET 20V, 22mΩ, 8A, Single N-Channel

Features

- Low On-Resistance
- 1.2V Drive
- ESD Diode-Protected Gate

Thermal Resistance Ratings

 $(1200 \text{mm}^2 \times 0.8 \text{mm})$

Parameter

• Pb-Free, Halogen Free and RoHS Compliance

Specifications

Absolute Maximum Ratings at $Ta = 25^{\circ}C$

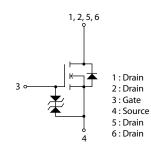
Parameter	Symbol	Value	Unit
Drain to Source Voltage	VDSS	20	V
Gate to Source Voltage	V _{GSS}	±9	V
Drain Current (DC)	ID	8	А
Drain Current (Pulse) PW≤10μs, duty cycle≤1%	I _{DP}	32	А
Power Dissipation When mounted on ceramic substrate $(1200mm^2 \times 0.8mm)$	PD	1.5	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	–55 to +150	°C

Symbol

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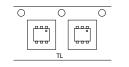
VDSS	R _{DS} (on) Max	ID Max	
20V	22mΩ@ 4.5V		
	28mΩ@ 2.5V	0.4	
	39mΩ@ 1.8V	8A	
	124mΩ@ 1.2V		

Electrical Connection N-Channel



Packing Type : TL

Marking



12-7		<u>ien</u>
191	7Y	191
1'Si	LΛ	'S I
121		11 I.
0		
4		

Junction to Ambient When mounted on ceramic substrate R_{0JA} 83.3

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Unit

°C/W

Value

ORDERING INFORMATION

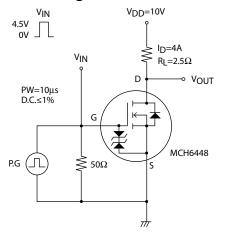
See detailed ordering and shipping information on page 5 of this data sheet.

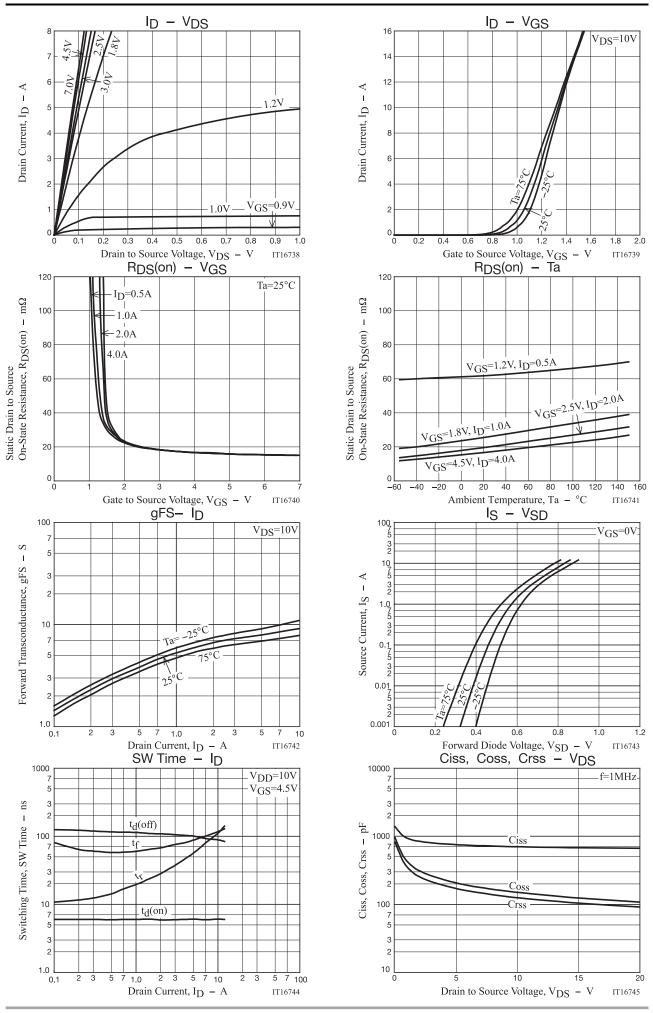
Electrical Characteristics at $Ta = 25^{\circ}C$

Parameter	O: week al		Value			
	Symbol	Conditions	min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	I _D =1mA, V _{GS} =0V	20			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =20V, V _{GS} =0V			1	μA
Gate to Source Leakage Current	IGSS	V _{GS} =±7.2V, V _{DS} =0V			±10	μA
Gate Threshold Voltage	V _{GS} (th)	V _{DS} =10V, I _D =1mA	0.3		1.0	V
Forward Transconductance	9FS	V _{DS} =10V, I _D =4A		7.7		S
	R _{DS} (on)1	I _D =4A, V _{GS} =4.5V		17	22	mΩ
Static Drain to Source On-State Resistance	R _{DS} (on)2	I _D =2A, V _{GS} =2.5V		20	28	mΩ
	R _{DS} (on)3	I _D =1A, V _{GS} =1.8V		26	39	mΩ
	R _{DS} (on)4	I _D =0.5A, V _{GS} =1.2V		62	124	mΩ
Input Capacitance	Ciss	V _{DS} =10V, f=1MHz		705		pF
Output Capacitance	Coss			150		pF
Reverse Transfer Capacitance	Crss			125		pF
Turn-ON Delay Time	t _d (on)			6		ns
Rise Time	tr			47		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit		103		ns
Fall Time	tf			81		ns
Total Gate Charge	Qg	V _{DS} =10V, V _{GS} =4.5V, I _D =8A		11.2		nC
Gate to Source Charge	Qgs			1.3		nC
Gate to Drain "Miller" Charge	Qgd	1		2.8		nC
Forward Diode Voltage	V _{SD}	IS=8A, VGS=0V		0.8	1.2	V

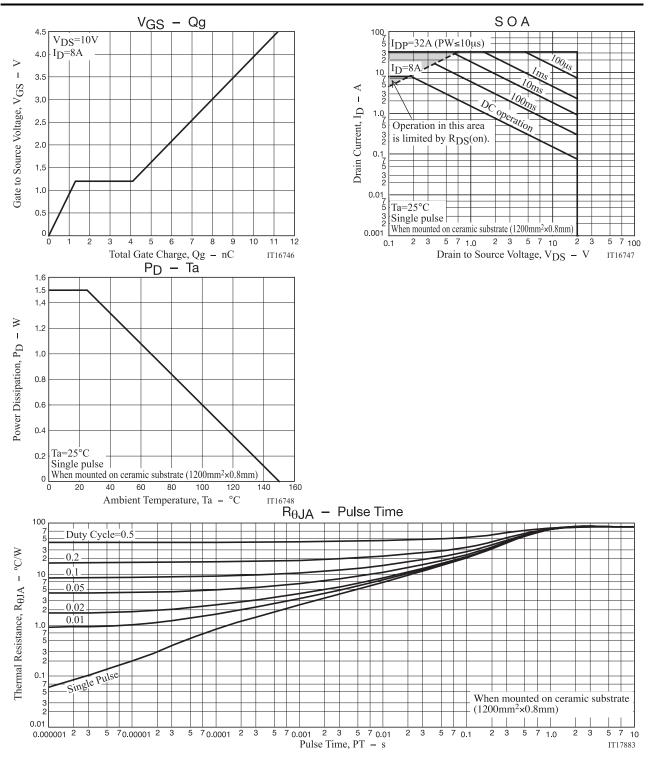
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Switching Time Test Circuit





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Package Dimensions

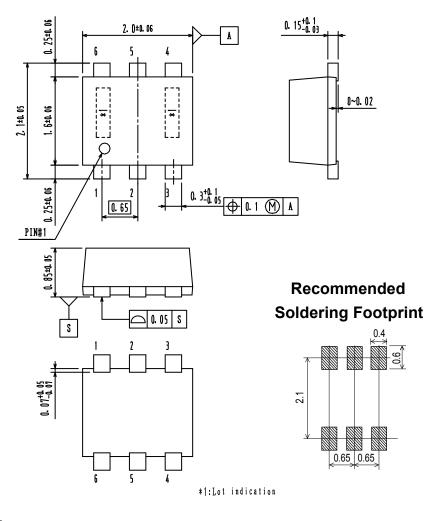
MCH6448-TL-H / MCH6448-TL-W

MCPH6

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unit : mm

- 1 : Drain
- 2 : Drain
- 3 : Gate
- 4 : Source
- 5 : Drain
- 6 : Drain



ORDERING INFORMATION

Device	Package	Shipping	Note	
MCH6448-TL-H	MCPH6	3,000 pcs. / Tape & Reel	Pb-Free	
MCH6448-TL-W	SC-88FL,SC-70-6,SOT-363	5,000 pcs. / Tape & Reel	and Halogen Free	

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub_link/Collateral/BRD8011-D.PDF

Note on usage : Since the MCH6448 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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